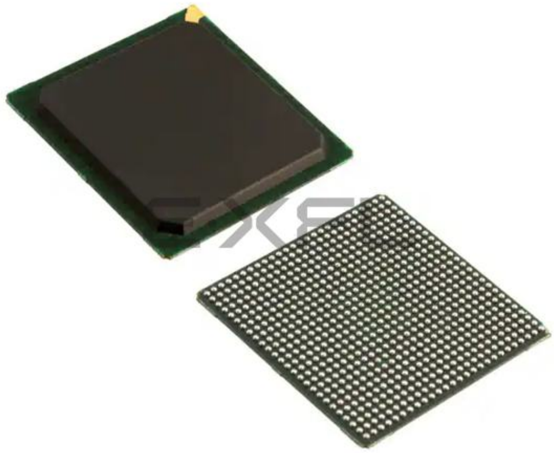
Microchip Technology - M1A3PE1500-FGG676I Datasheet



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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	276480
Number of I/O	444
Number of Gates	1500000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	676-BGA
Supplier Device Package	676-FBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/m1a3pe1500-fgg676i

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Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Table of Contents

ProASIC3E Device Family Overview

ProASIC3E DC and Switching Characteristics

Pin Descriptions and Packaging

Package Pin Assignments

Datasheet Information

Advanced Architecture

The proprietary ProASIC3E architecture provides granularity comparable to standard-cell ASICs. The ProASIC3E device consists of five distinct and programmable architectural features (Figure 1-1 on page 3):

- FPGA VersaTiles
- Dedicated FlashROM
- Dedicated SRAM/FIFO memory
- Extensive CCCs and PLLs
- Pro I/O structure

The FPGA core consists of a sea of VersaTiles. Each VersaTile can be configured as a three-input logic function, a D-flip-flop (with or without enable), or a latch by programming the appropriate flash switch interconnections. The versatility of the ProASIC3E core tile as either a three-input lookup table (LUT) equivalent or as a D-flip-flop/latch with enable allows for efficient use of the FPGA fabric. The VersaTile capability is unique to the ProASIC family of third-generation architecture Flash FPGAs. VersaTiles are connected with any of the four levels of routing hierarchy. Flash switches are distributed throughout the device to provide nonvolatile, reconfigurable interconnect programming. Maximum core utilization is possible for virtually any design.

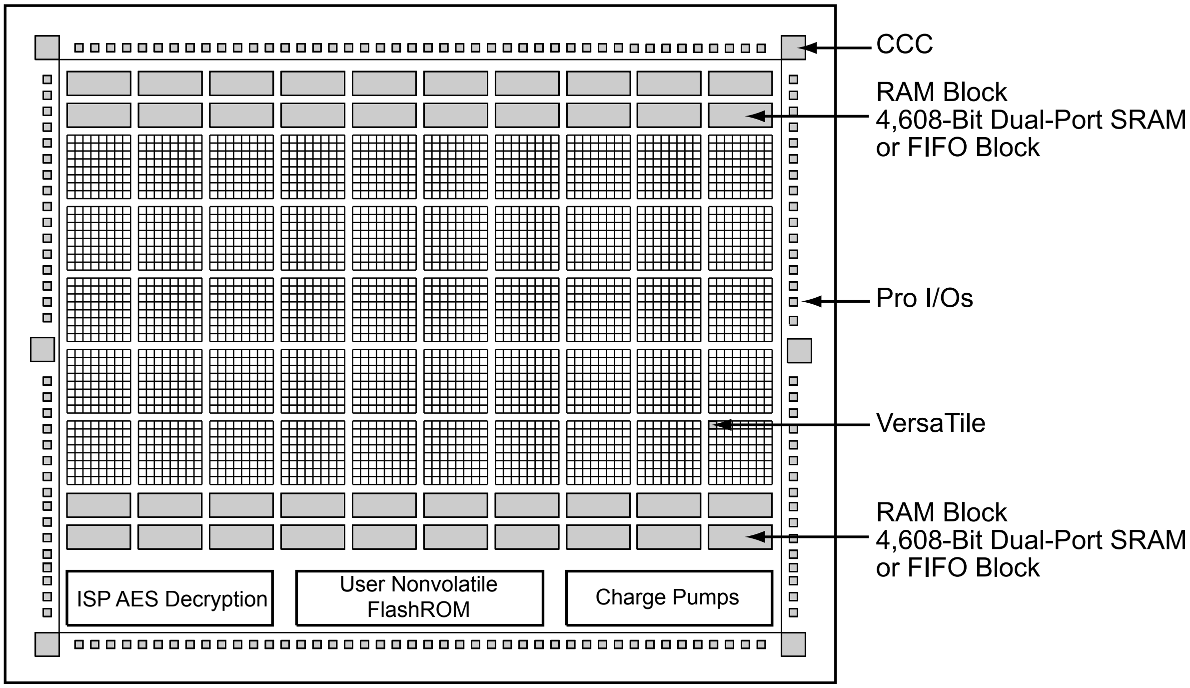

Figure 1-1 • **ProASIC3E Device Architecture Overview**

Table 2-8 • **Summary of I/O Input Buffer Power (per pin) – Default I/O Software Settings (continued)**

	VMV (V)	Static Power PDC2 (mW)[1]	Dynamic Power PAC9 (µW/MHz)[2]
HSTL (I)	1.5	0.17	2.03
HSTL (II)	1.5	0.17	2.03
SSTL2 (I)	2.5	1.38	4.48
SSTL2 (II)	2.5	1.38	4.48
SSTL3 (I)	3.3	3.21	9.26
SSTL3 (II)	3.3	3.21	9.26
Differential			
LVDS/B-LVDS/M-LVDS	2.5	2.26	1.50
LVPECL	3.3	5.71	2.17

Notes:

1. *PDC2 is the static power (where applicable) measured on VMV.*
2. *PAC9 is the total dynamic power measured on VCC and VMV.*
3. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8b specification.*

Table 2-9 • **Summary of I/O Output Buffer Power (per pin) – Default I/O Software Settings** [1]

	C_{LOAD} (pF)	VCCI (V)	Static Power PDC3 (mW)[2]	Dynamic Power PAC10 (µW/MHz)[3]
Single-Ended				
3.3 V LVTTL/LVCMOS	35	3.3	–	474.70
3.3 V LVTTL/LVCMOS Wide Range[4]	35	3.3	–	474.70
2.5 V LVCMOS	35	2.5	–	270.73
1.8 V LVCMOS	35	1.8	–	151.78
1.5 V LVCMOS (JESD8-11)	35	1.5	–	104.55
3.3 V PCI	10	3.3	–	204.61
3.3 V PCI-X	10	3.3	–	204.61
Voltage-Referenced				
3.3 V GTL	10	3.3	–	24.08
2.5 V GTL	10	2.5	–	13.52
3.3 V GTL+	10	3.3	–	24.10
2.5 V GTL+	10	2.5	–	13.54
HSTL (I)	20	1.5	7.08	26.22
HSTL (II)	20	1.5	13.88	27.22
SSTL2 (I)	30	2.5	16.69	105.56
SSTL2 (II)	30	2.5	25.91	116.60

Notes:

1. *Dynamic power consumption is given for standard load and software default drive strength and output slew.*
2. *PDC3 is the static power (where applicable) measured on VCCI.*
3. *PAC10 is the total dynamic power measured on VCC and VCCI.*
4. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.*

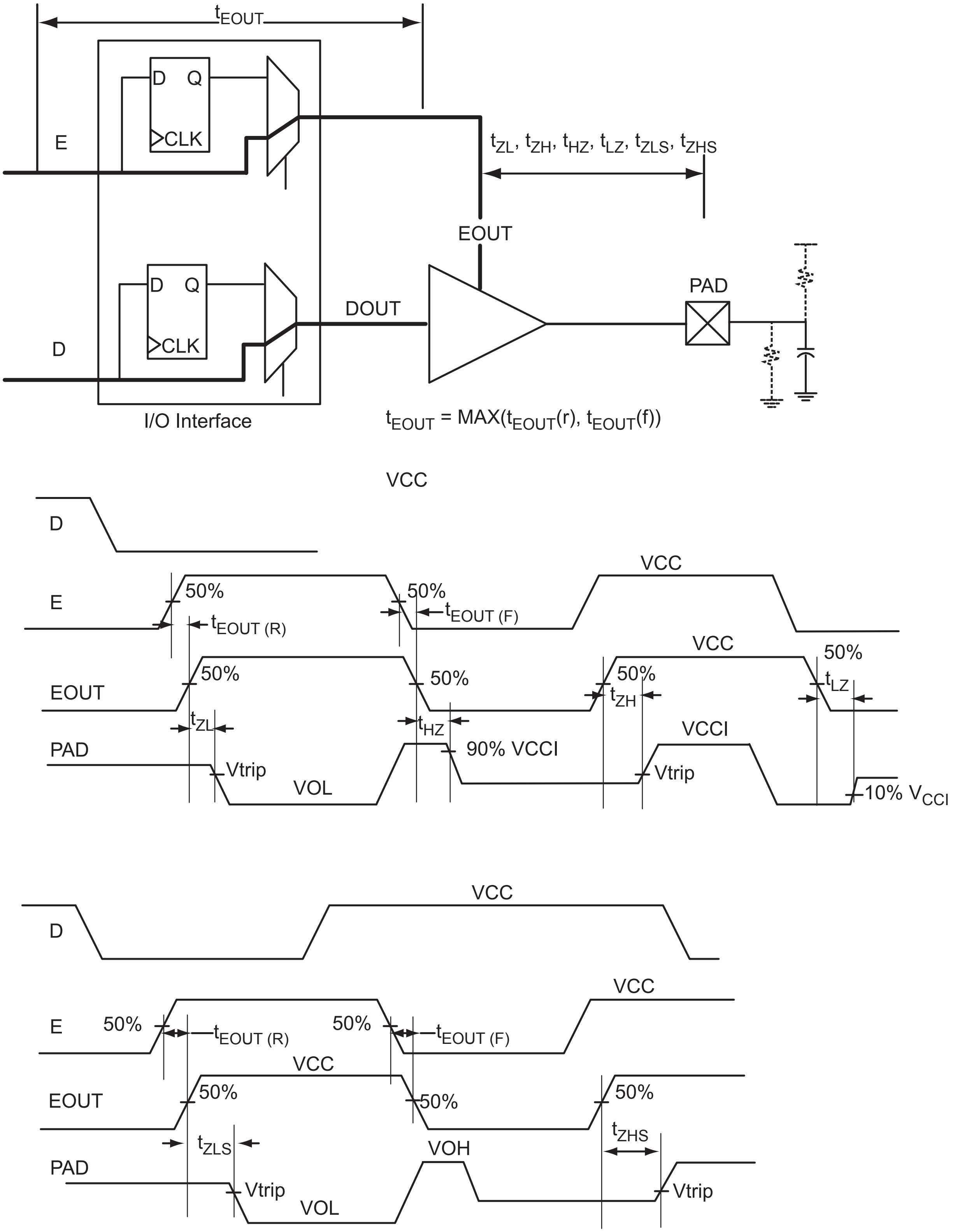

Figure 2-5 • **Tristate Output Buffer Timing Model and Delays (example)**

Overview of I/O Performance

Summary of I/O DC Input and Output Levels – Default I/O Software Settings

Table 2-13 • **Summary of Maximum and Minimum DC Input and Output Levels Applicable to Commercial and Industrial Conditions**

I/O Standard	Drive Strength	Equivalent Software Default Drive Strength Option[1]	Slew Rate	VIL		VIH		VOL	VOH	IOL[3]	IOH[3]
				Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA
3.3 V LVTTL / 3.3 V LVCMOS	12 mA	12 mA	High	–0.3	0.8	2	3.6	0.4	2.4	12	12
3.3 V LVCMOS Wide Range	100 µA	12 mA	High	–0.3	0.8	2	3.6	0.2	VCCI – 0.2	0.1	0.1
2.5 V LVCMOS	12 mA	12 mA	High	–0.3	0.7	1.7	3.6	0.7	1.7	12	12
1.8 V LVCMOS	12 mA	12 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI – 0.45	12	12
1.5 V LVCMOS	12 mA	12 mA	High	–0.3	0.30 * VCCI	0.7 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	12	12
3.3 V PCI	Per PCI Specification										
3.3 V PCI-X	Per PCI-X Specification										
3.3 V GTL	20 mA[2]	20 mA[2]	High	–0.3	VREF – 0.05	VREF + 0.05	3.6	0.4	–	20	20
2.5 V GTL	20 mA[2]	20 mA[2]	High	–0.3	VREF – 0.05	VREF + 0.05	3.6	0.4	–	20	20
3.3 V GTL+	35 mA	35 mA	High	–0.3	VREF – 0.1	VREF + 0.1	3.6	0.6	–	35	35
2.5 V GTL+	33 mA	33 mA	High	–0.3	VREF – 0.1	VREF + 0.1	3.6	0.6	–	33	33
HSTL (I)	8 mA	8 mA	High	–0.3	VREF – 0.1	VREF + 0.1	3.6	0.4	VCCI – 0.4	8	8
HSTL (II)	15 mA[2]	15 mA[2]	High	–0.3	VREF – 0.1	VREF + 0.1	3.6	0.4	VCCI – 0.4	15	15
SSTL2 (I)	15 mA	15 mA	High	–0.3	VREF – 0.2	VREF + 0.2	3.6	0.54	VCCI – 0.62	15	15
SSTL2 (II)	18 mA	18 mA	High	–0.3	VREF – 0.2	VREF + 0.2	3.6	0.35	VCCI – 0.43	18	18
SSTL3 (I)	14 mA	14 mA	High	–0.3	VREF – 0.2	VREF + 0.2	3.6	0.7	VCCI – 1.1	14	14
SSTL3 (II)	21 mA	21 mA	High	–0.3	VREF – 0.2	VREF + 0.2	3.6	0.5	VCCI – 0.9	21	21

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *Output drive strength is below JEDEC specification.*
3. *Currents are measured at 85°C junction temperature.*
4. *Output Slew Rates can be extracted from IBIS Models, located at http://www.microsemi.com/index.php?option=com_content&id=1671&lang=en&view=article.*

Summary of I/O Timing Characteristics – Default I/O Software Settings

Table 2-15 • **Summary of AC Measuring Points**

Standard	Input Reference Voltage (VREF_TYP)	Board Termination Voltage (VTT_REF)	Measuring Trip Point (Vtrip)
3.3 V LVTTL / 3.3 V LVCMOS	–	–	1.4 V
3.3 V LVCMOS Wide Range	–	–	1.4 V
2.5 V LVCMOS	–	–	1.2 V
1.8 V LVCMOS	–	–	0.90 V
1.5 V LVCMOS	–	–	0.75 V
3.3 V PCI	–	–	0.285 * VCCI (RR) 0.615 * VCCI (FF))
3.3 V PCI-X	–	–	0.285 * VCCI (RR) 0.615 * VCCI (FF)
3.3 V GTL	0.8 V	1.2 V	VREF
2.5 V GTL	0.8 V	1.2 V	VREF
3.3 V GTL+	1.0 V	1.5 V	VREF
2.5 V GTL+	1.0 V	1.5 V	VREF
HSTL (I)	0.75 V	0.75 V	VREF
HSTL (II)	0.75 V	0.75 V	VREF
SSTL2 (I)	1.25 V	1.25 V	VREF
SSTL2 (II)	1.25 V	1.25 V	VREF
SSTL3 (I)	1.5 V	1.485 V	VREF
SSTL3 (II)	1.5 V	1.485 V	VREF
LVDS	–	–	Cross point
LVPECL	–	–	Cross point

Table 2-16 • **I/O AC Parameter Definitions**

Parameter	Definition
t_{DP}	Data to Pad delay through the Output Buffer
t_{PY}	Pad to Data delay through the Input Buffer with Schmitt trigger disabled
t_{DOUT}	Data to Output Buffer delay through the I/O interface
t_{EOUT}	Enable to Output Buffer Tristate Control delay through the I/O interface
t_{DIN}	Input Buffer to Data delay through the I/O interface
t_{PYS}	Pad to Data delay through the Input Buffer with Schmitt trigger enabled
t_{HZ}	Enable to Pad delay through the Output Buffer—High to Z
t_{ZH}	Enable to Pad delay through the Output Buffer—Z to High
t_{LZ}	Enable to Pad delay through the Output Buffer—Low to Z
t_{ZL}	Enable to Pad delay through the Output Buffer—Z to Low
t_{ZHS}	Enable to Pad delay through the Output Buffer with delayed enable—Z to High
t_{ZLS}	Enable to Pad delay through the Output Buffer with delayed enable—Z to Low

***Table 2-40* • 1.8 V LVCMOS Low Slew**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	15.84	0.04	1.45	1.91	0.43	15.65	15.84	2.78	1.58	17.89	18.07	ns
	–1	0.56	13.47	0.04	1.23	1.62	0.36	13.31	13.47	2.37	1.35	15.22	15.37	ns
	–2	0.49	11.83	0.03	1.08	1.42	0.32	11.69	11.83	2.08	1.18	13.36	13.50	ns
4 mA	Std.	0.66	11.39	0.04	1.45	1.91	0.43	11.60	10.76	3.26	2.77	13.84	12.99	ns
	–1	0.56	9.69	0.04	1.23	1.62	0.36	9.87	9.15	2.77	2.36	11.77	11.05	ns
	–2	0.49	8.51	0.03	1.08	1.42	0.32	8.66	8.03	2.43	2.07	10.33	9.70	ns
6 mA	Std.	0.66	8.97	0.04	1.45	1.91	0.43	9.14	8.10	3.57	3.36	11.37	10.33	ns
	–1	0.56	7.63	0.04	1.23	1.62	0.36	7.77	6.89	3.04	2.86	9.67	8.79	ns
	–2	0.49	6.70	0.03	1.08	1.42	0.32	6.82	6.05	2.66	2.51	8.49	7.72	ns
8 mA	Std.	0.66	8.35	0.04	1.45	1.91	0.43	8.50	7.59	3.64	3.52	10.74	9.82	ns
	–1	0.56	7.10	0.04	1.23	1.62	0.36	7.23	6.45	3.10	3.00	9.14	8.35	ns
	–2	0.49	6.24	0.03	1.08	1.42	0.32	6.35	5.66	2.72	2.63	8.02	7.33	ns
12 mA	Std.	0.66	7.94	0.04	1.45	1.91	0.43	8.09	7.56	3.74	4.11	10.32	9.80	ns
	–1	0.56	6.75	0.04	1.23	1.62	0.36	6.88	6.43	3.18	3.49	8.78	8.33	ns
	–2	0.49	5.93	0.03	1.08	1.42	0.32	6.04	5.65	2.79	3.07	7.71	7.32	ns
16 mA	Std.	0.66	7.94	0.04	1.45	1.91	0.43	8.09	7.56	3.74	4.11	10.32	9.80	ns
	–1	0.56	6.75	0.04	1.23	1.62	0.36	6.88	6.43	3.18	3.49	8.78	8.33	ns
	–2	0.49	5.93	0.03	1.08	1.42	0.32	6.04	5.65	2.79	3.07	7.71	7.32	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

HSTL Class I

High-Speed Transceiver Logic is a general-purpose high-speed 1.5 V bus standard (EIA/JESD8-6). ProASIC3E devices support Class I. This provides a differential amplifier input buffer and a push-pull output buffer.

***Table 2-60* • Minimum and Maximum DC Input and Output Levels**

HSTL Class I	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL	IIH
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[1]	Max. mA[1]	µA[2]	µA[2]
8 mA	–0.3	VREF – 0.1	VREF + 0.1	3.6	0.4	VCCI – 0.4	8	8	39	32	10	10

Notes:

1. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
2. *Currents are measured at 85°C junction temperature.*

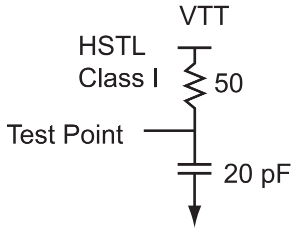

***Figure 2-16* • AC Loading**

***Table 2-61* • AC Waveforms, Measuring Points, and Capacitive Loads**

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	VTT (typ.) (V)	C_{LOAD} (pF)
VREF – 0.1	VREF + 0.1	0.75	0.75	0.75	20

*Note: *Measuring point = Vtrip. See Table 2-15 on page 2-18 for a complete table of trip points.*

Timing Characteristics

***Table 2-62* • HSTL Class I**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V,
Worst-Case VCCI = .4 V, VREF = 0.75 V

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
Std.	0.66	3.18	0.04	2.12	0.43	3.24	3.14			5.47	5.38	ns
–1	0.56	2.70	0.04	1.81	0.36	2.75	2.67			4.66	4.58	ns
–2	0.49	2.37	0.03	1.59	0.32	2.42	2.35			4.09	4.02	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.

Table 2-84 • Parameter Definition and Measuring Nodes

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t_{OCLKQ}	Clock-to-Q of the Output Data Register	H, DOUT
t_{OSUD}	Data Setup Time for the Output Data Register	F, H
t_{OHD}	Data Hold Time for the Output Data Register	F, H
t_{OSUE}	Enable Setup Time for the Output Data Register	G, H
t_{OHE}	Enable Hold Time for the Output Data Register	G, H
t_{OPRE2Q}	Asynchronous Preset-to-Q of the Output Data Register	L, DOUT
$t_{OREMPRE}$	Asynchronous Preset Removal Time for the Output Data Register	L, H
$t_{ORECPRE}$	Asynchronous Preset Recovery Time for the Output Data Register	L, H
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	H, EOUT
t_{OESUD}	Data Setup Time for the Output Enable Register	J, H
t_{OEHD}	Data Hold Time for the Output Enable Register	J, H
t_{OESUE}	Enable Setup Time for the Output Enable Register	K, H
t_{OEHE}	Enable Hold Time for the Output Enable Register	K, H
$t_{OEPRE2Q}$	Asynchronous Preset-to-Q of the Output Enable Register	I, EOUT
$t_{OEREMPRE}$	Asynchronous Preset Removal Time for the Output Enable Register	I, H
$t_{OERECPRE}$	Asynchronous Preset Recovery Time for the Output Enable Register	I, H
t_{ICLKQ}	Clock-to-Q of the Input Data Register	A, E
t_{ISUD}	Data Setup Time for the Input Data Register	C, A
t_{IHD}	Data Hold Time for the Input Data Register	C, A
t_{ISUE}	Enable Setup Time for the Input Data Register	B, A
t_{IHE}	Enable Hold Time for the Input Data Register	B, A
t_{IPRE2Q}	Asynchronous Preset-to-Q of the Input Data Register	D, E
$t_{IREMPRE}$	Asynchronous Preset Removal Time for the Input Data Register	D, A
$t_{IRECPRE}$	Asynchronous Preset Recovery Time for the Input Data Register	D, A

Note: *See Figure 2-25 on page 2-53 for more information.

Output DDR Module

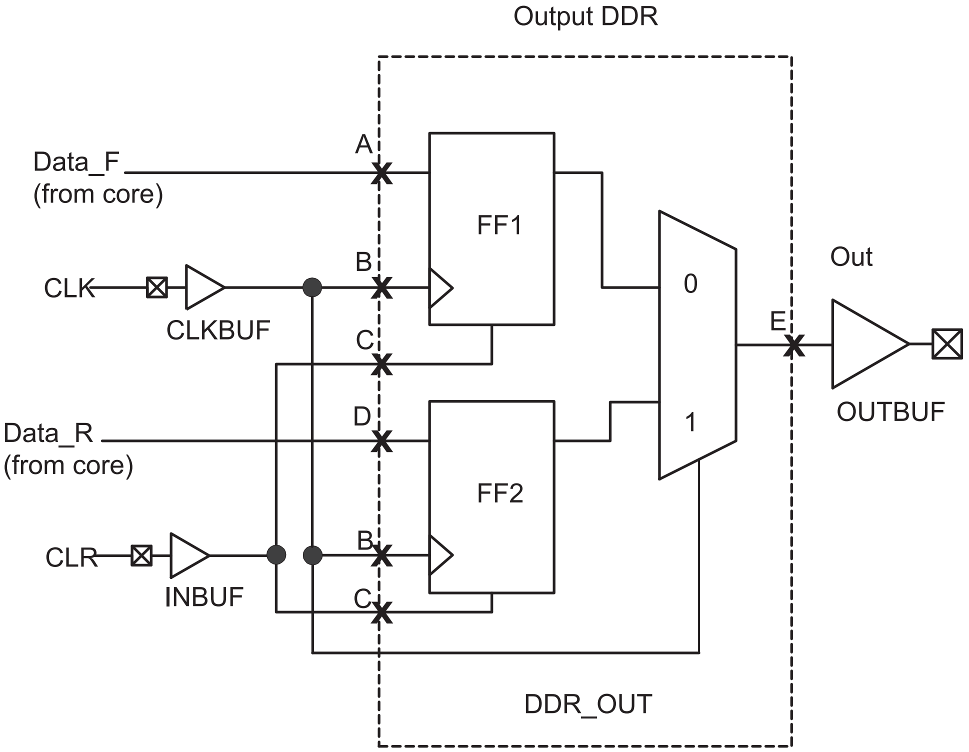

Figure 2-32 • **Output DDR Timing Model**

Table 2-91 • **Parameter Definitions**

Parameter Name	Parameter Definition	Measuring Nodes (from, to)
$t_{DDROCLKQ}$	Clock-to-Out	B, E
$t_{DDROCLR2Q}$	Asynchronous Clear-to-Out	C, E
$t_{DDROREMCLR}$	Clear Removal	C, B
$t_{DDRORECCLR}$	Clear Recovery	C, B
$t_{DDROSUD1}$	Data Setup Data_F	A, B
$t_{DDROSUD2}$	Data Setup Data_R	D, B
$t_{DDROHD1}$	Data Hold Data_F	A, B
$t_{DDROHD2}$	Data Hold Data_R	D, B

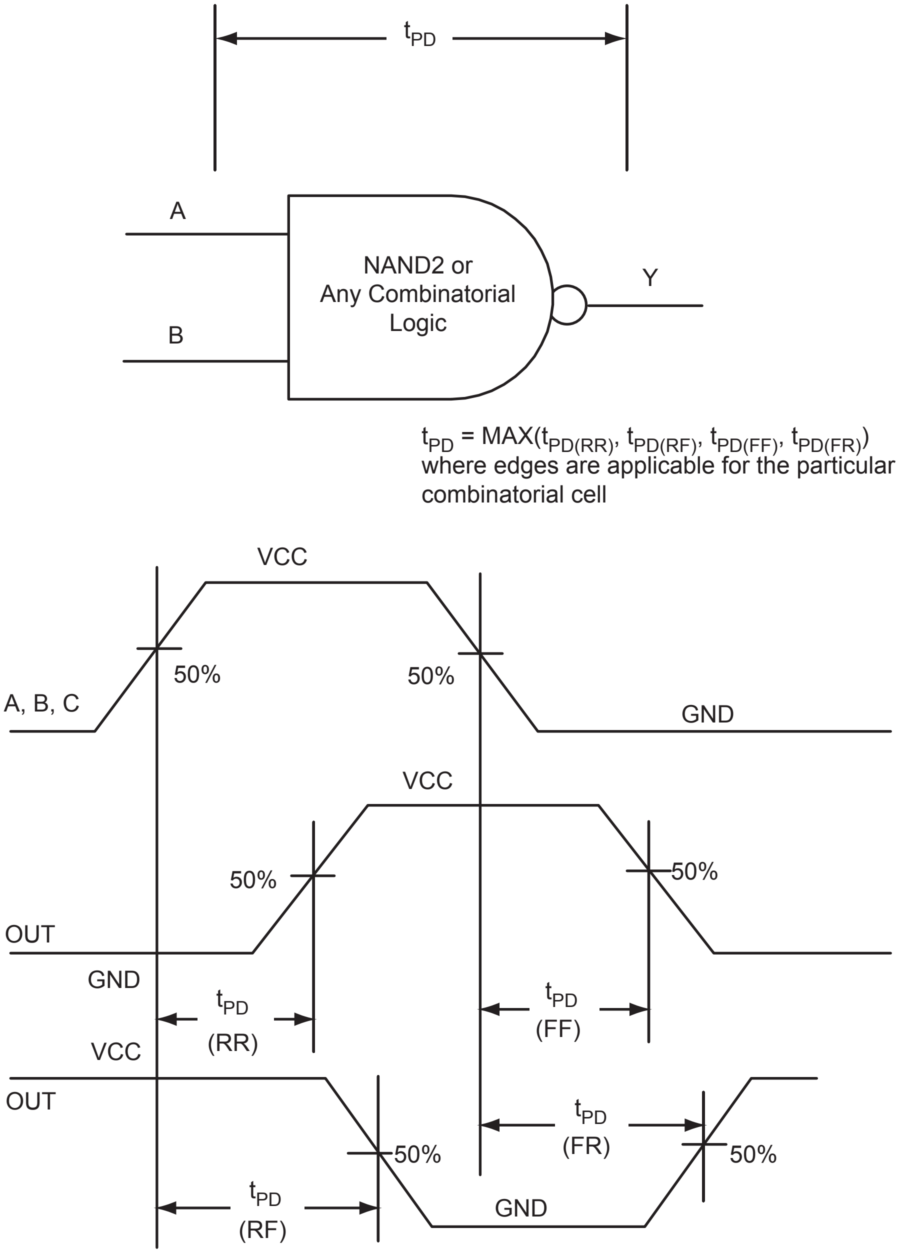

Figure 2-35 • **Timing Model and Waveforms**

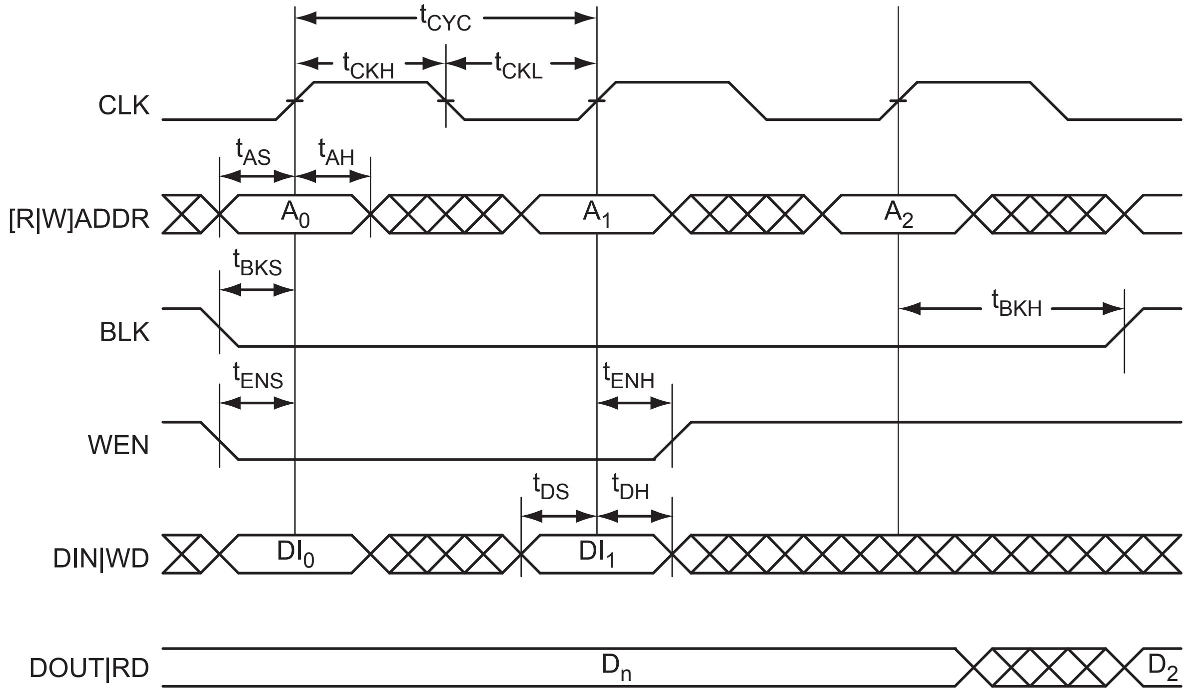

Figure 2-43 • **RAM Write, Output Retained. Applicable to Both RAM4K9 and RAM512x18.**

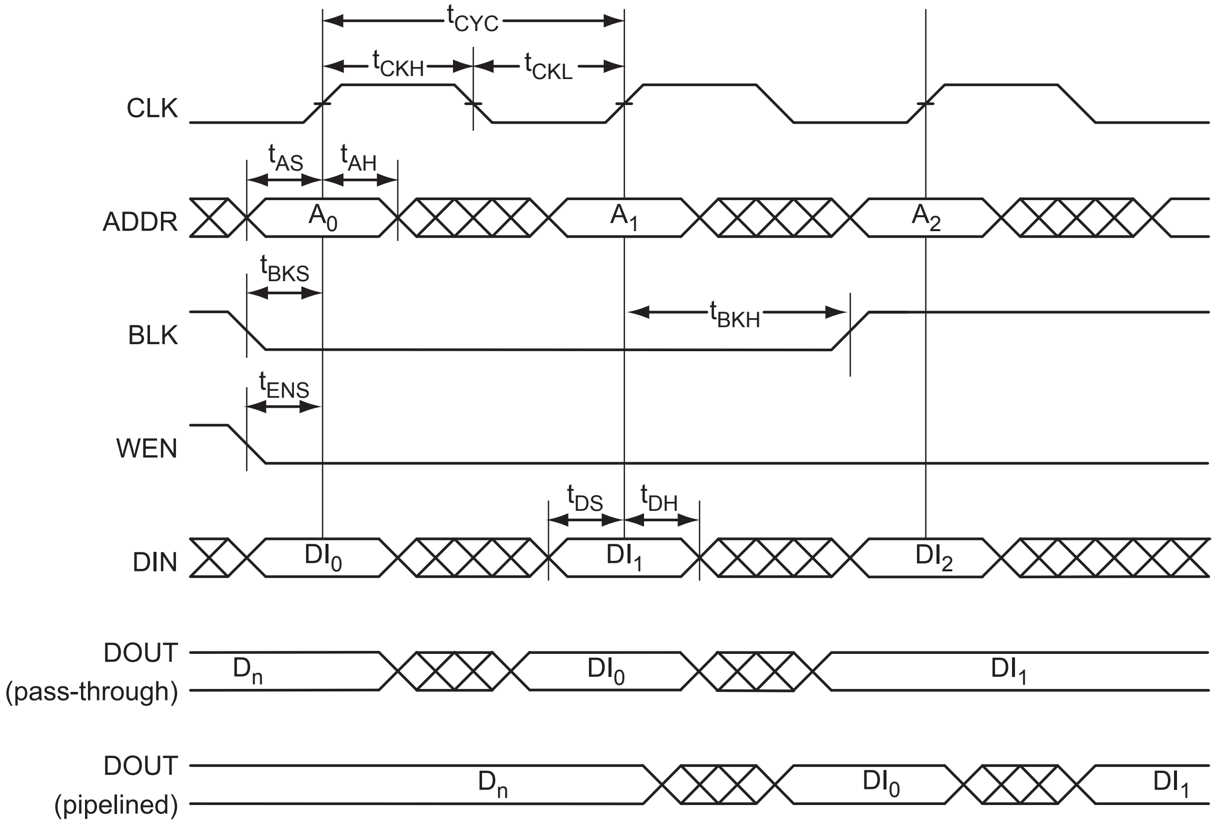

Figure 2-44 • **RAM Write, Output as Write Data. Applicable to RAM4K9 Only.**

***Table 2-100* • RAM512X18**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	–2	–1	Std.	Units
t_{AS}	Address setup time	0.25	0.28	0.33	ns
t_{AH}	Address hold time	0.00	0.00	0.00	ns
t_{ENS}	REN, WEN setup time	0.18	0.20	0.24	ns
t_{ENH}	REN, WEN hold time	0.06	0.07	0.08	ns
t_{DS}	Input data (WD) setup time	0.18	0.21	0.25	ns
t_{DH}	Input data (WD) hold time	0.00	0.00	0.00	ns
t_{CKQ1}	Clock High to new data valid on RD (output retained)	2.16	2.46	2.89	ns
t_{CKQ2}	Clock High to new data valid on RD (pipelined)	0.90	1.02	1.20	ns
t_{C2CRWH}[1]	Address collision clk-to-clk delay for reliable read access after write on same address—Applicable to Opening Edge	0.50	0.43	0.38	ns
t_{C2CWRH}[1]	Address collision clk-to-clk delay for reliable write access after read on same address— Applicable to Opening Edge	0.59	0.50	0.44	ns
t_{RSTBQ}	RESET Low to data out Low on RD (flow-through)	0.92	1.05	1.23	ns
	RESET Low to data out Low on RD (pipelined)	0.92	1.05	1.23	ns
$t_{REMRSTB}$	RESET removal	0.29	0.33	0.38	ns
$t_{RECRSTB}$	RESET recovery	1.50	1.71	2.01	ns
$t_{MPWRSTB}$	RESET minimum pulse width	0.21	0.24	0.29	ns
t_{CYC}	Clock cycle time	3.23	3.68	4.32	ns
F_{MAX}	Maximum frequency	310	272	231	MHz

Notes:

1. *For more information, refer to the application note Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-5 for derating values.*

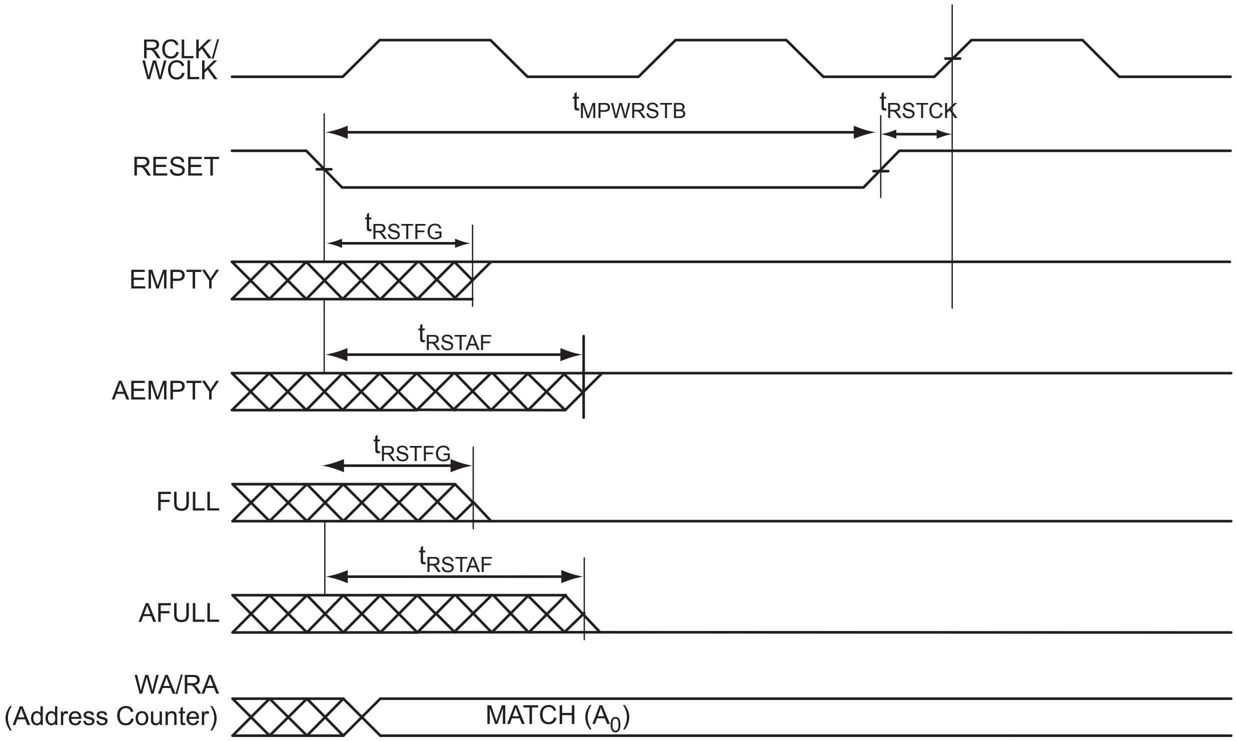

***Figure 2-49* • FIFO Reset**

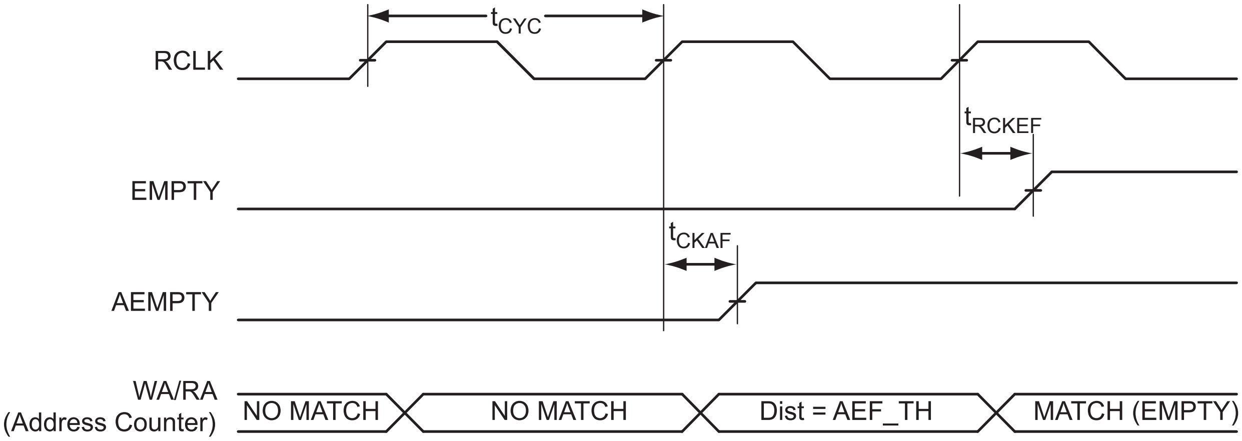

***Figure 2-50* • FIFO EMPTY Flag and AEMPTY Flag Assertion**

FG324	
Pin Number	**A3PE3000 FBGA**
A1	GND
A2	IO08NDB0V0
A3	IO08PDB0V0
A4	IO10NDB0V1
A5	IO10PDB0V1
A6	IO12PDB0V1
A7	GND
A8	IO32NDB0V3
A9	IO32PDB0V3
A10	IO42PPB1V0
A11	IO52NPB1V1
A12	GND
A13	IO66NDB1V3
A14	IO72NDB1V3
A15	IO72PDB1V3
A16	IO74NDB1V4
A17	IO74PDB1V4
A18	GND
B1	IO305PDB7V3
B2	GAB2/IO308PDB7V4
B3	GAA0/IO00NPB0V0
B4	VCCIB0
B5	GNDQ
B6	IO12NDB0V1
B7	IO18NDB0V2
B8	VCCIB0
B9	IO42NPB1V0
B10	IO44NDB1V0
B11	VCCIB1
B12	IO52PPB1V1
B13	IO66PDB1V3
B14	GNDQ
B15	VCCIB1
B16	GBA0/IO81NDB1V4
B17	GBA1/IO81PDB1V4
B18	IO88PDB2V0

FG324	
Pin Number	**A3PE3000 FBGA**
C1	IO305NDB7V3
C2	IO308NDB7V4
C3	GAA2/IO309PPB7V4
C4	GAA1/IO00PPB0V0
C5	VMV0
C6	IO14NDB0V1
C7	IO18PDB0V2
C8	IO40NDB0V4
C9	IO40PDB0V4
C10	IO44PDB1V0
C11	IO56NDB1V1
C12	IO64NDB1V2
C13	IO64PDB1V2
C14	VMV1
C15	GBC0/IO79NDB1V4
C16	GBC1/IO79PDB1V4
C17	GBB2/IO83PPB2V0
C18	IO88NDB2V0
D1	IO303PDB7V3
D2	VCCIB7
D3	GAC2/IO307PPB7V4
D4	IO309NPB7V4
D5	GAB1/IO01PPB0V0
D6	IO14PDB0V1
D7	IO24NDB0V2
D8	IO24PDB0V2
D9	IO28PDB0V3
D10	IO48NDB1V0
D11	IO56PDB1V1
D12	IO60PPB1V2
D13	GBB0/IO80NDB1V4
D14	GBB1/IO80PDB1V4
D15	GBA2/IO82PDB2V0
D16	IO83NPB2V0
D17	VCCIB2
D18	IO90PDB2V1

FG324	
Pin Number	**A3PE3000 FBGA**
E1	IO303NDB7V3
E2	GNDQ
E3	VMV7
E4	IO307NPB7V4
E5	VCCPLA
E6	GAB0/IO01NPB0V0
E7	VCCIB0
E8	GND
E9	IO28NDB0V3
E10	IO48PDB1V0
E11	GND
E12	VCCIB1
E13	IO60NPB1V2
E14	VCCPLB
E15	IO82NDB2V0
E16	VMV2
E17	GNDQ
E18	IO90NDB2V1
F1	IO299NDB7V3
F2	IO299PDB7V3
F3	IO295PDB7V2
F4	IO295NDB7V2
F5	VCOMPLA
F6	IO291PPB7V2
F7	GAC0/IO02NDB0V0
F8	GAC1/IO02PDB0V0
F9	IO26PDB0V3
F10	IO34PDB0V4
F11	IO58NDB1V2
F12	IO58PDB1V2
F13	IO94PPB2V1
F14	VCOMPLB
F15	GBC2/IO84PDB2V0
F16	IO84NDB2V0
F17	IO92NDB2V1
F18	IO92PDB2V1

FG484	
Pin Number	**A3PE600 Function**
V15	IO69NDB4V0
V16	GDB2/IO69PDB4V0
V17	TDI
V18	GNDQ
V19	TDO
V20	GND
V21	NC
V22	IO63NDB3V1
W1	NC
W2	NC
W3	NC
W4	GND
W5	IO100NDB5V2
W6	GEB2/IO100PDB5V2
W7	IO99NDB5V2
W8	IO88NDB5V0
W9	IO88PDB5V0
W10	IO89NDB5V0
W11	IO80NDB4V1
W12	IO81NDB4V1
W13	IO81PDB4V1
W14	IO70NDB4V0
W15	GDC2/IO70PDB4V0
W16	IO68NDB4V0
W17	GDA2/IO68PDB4V0
W18	TMS
W19	GND
W20	NC
W21	NC
W22	NC
Y1	VCCIB6
Y2	NC
Y3	NC
Y4	IO98NDB5V2
Y5	GND
Y6	IO94NDB5V1
Y7	IO94PDB5V1
Y8	VCC
Y9	VCC
Y10	IO89PDB5V0
Y11	IO80PDB4V1
Y12	IO78NPB4V1
Y13	NC
Y14	VCC
Y15	VCC
Y16	NC
Y17	NC
Y18	GND
Y19	NC
Y20	NC
Y21	NC
Y22	VCCIB3

FG484	
Pin Number	**A3PE3000 Function**
N17	IO132NPB3V2
N18	IO117NPB3V0
N19	IO132PPB3V2
N20	GNDQ
N21	IO126NDB3V1
N22	IO128PDB3V1
P1	IO247PDB6V1
P2	IO253PDB6V2
P3	IO270NPB6V4
P4	IO261NPB6V3
P5	IO249PPB6V1
P6	IO259PDB6V3
P7	IO259NDB6V3
P8	VCCIB6
P9	GND
P10	VCC
P11	VCC
P12	VCC
P13	VCC
P14	GND
P15	VCCIB3
P16	GDB0/IO152NPB3V4
P17	IO136NDB3V2
P18	IO136PDB3V2
P19	IO138PDB3V3
P20	VMV3
P21	IO130PDB3V2
P22	IO128NDB3V1
R1	IO247NDB6V1
R2	IO245PDB6V1
R3	VCC
R4	IO249NPB6V1
R5	IO251NDB6V2
R6	IO251PDB6V2
R7	GEC0/IO236NPB6V0
R8	VMV5

FG484	
Pin Number	**A3PE3000 Function**
R9	VCCIB5
R10	VCCIB5
R11	IO196NDB5V0
R12	IO196PDB5V0
R13	VCCIB4
R14	VCCIB4
R15	VMV3
R16	VCCPLD
R17	GDB1/IO152PPB3V4
R18	GDC1/IO151PDB3V4
R19	IO138NDB3V3
R20	VCC
R21	IO130NDB3V2
R22	IO134PDB3V2
T1	IO243PPB6V1
T2	IO245NDB6V1
T3	IO243NPB6V1
T4	IO241PDB6V0
T5	IO241NDB6V0
T6	GEC1/IO236PPB6V0
T7	VCOMPLE
T8	GNDQ
T9	GEA2/IO233PPB5V4
T10	IO206NDB5V1
T11	IO202NDB5V1
T12	IO194NDB5V0
T13	IO186NDB4V4
T14	IO186PDB4V4
T15	GNDQ
T16	VCOMPLD
T17	VJTAG
T18	GDC0/IO151NDB3V4
T19	GDA1/IO153PDB3V4
T20	IO144PDB3V3
T21	IO140PDB3V3
T22	IO134NDB3V2

FG484	
Pin Number	**A3PE3000 Function**
U1	IO240PPB6V0
U2	IO238PDB6V0
U3	IO238NDB6V0
U4	GEB1/IO235PDB6V0
U5	GEB0/IO235NDB6V0
U6	VMV6
U7	VCCPLE
U8	IO233NPB5V4
U9	IO222PPB5V3
U10	IO206PDB5V1
U11	IO202PDB5V1
U12	IO194PDB5V0
U13	IO176NDB4V2
U14	IO176PDB4V2
U15	VMV4
U16	TCK
U17	VPUMP
U18	TRST
U19	GDA0/IO153NDB3V4
U20	IO144NDB3V3
U21	IO140NDB3V3
U22	IO142PDB3V3
V1	IO239PDB6V0
V2	IO240NPB6V0
V3	GND
V4	GEA1/IO234PDB6V0
V5	GEA0/IO234NDB6V0
V6	GNDQ
V7	GEC2/IO231PDB5V4
V8	IO222NPB5V3
V9	IO204NDB5V1
V10	IO204PDB5V1
V11	IO195NDB5V0
V12	IO195PDB5V0
V13	IO178NDB4V3
V14	IO178PDB4V3

FG896	
Pin Number	**A3PE3000 Function**
AK28	GND
AK29	GND
B1	GND
B2	GND
B3	GAA2/IO309PPB7V4
B4	VCC
B5	IO14PPB0V1
B6	VCC
B7	IO07PPB0V0
B8	IO09PDB0V1
B9	IO15PPB0V1
B10	IO19NDB0V2
B11	IO19PDB0V2
B12	IO29NDB0V3
B13	IO29PDB0V3
B14	IO31PPB0V3
B15	IO37NDB0V4
B16	IO37PDB0V4
B17	IO41PDB1V0
B18	IO51NDB1V1
B19	IO59PDB1V2
B20	IO53PDB1V1
B21	IO53NDB1V1
B22	IO61NDB1V2
B23	IO61PDB1V2
B24	IO69NPB1V3
B25	VCC
B26	GBC0/IO79NPB1V4
B27	VCC
B28	IO64NPB1V2
B29	GND
B30	GND
C1	GND
C2	IO309NPB7V4
C3	VCC
C4	GAA0/IO00NPB0V0
C5	VCCIB0
C6	IO03PDB0V0
C7	IO03NDB0V0
C8	GAB1/IO01PDB0V0
C9	IO05PDB0V0
C10	IO15NPB0V1
C11	IO25NDB0V3
C12	IO25PDB0V3
C13	IO31NPB0V3
C14	IO27NDB0V3
C15	IO39NDB0V4
C16	IO39PDB0V4
C17	IO55PPB1V1
C18	IO51PDB1V1
C19	IO59NDB1V2
C20	IO63NDB1V2
C21	IO63PDB1V2
C22	IO67NDB1V3
C23	IO67PDB1V3
C24	IO75NDB1V4
C25	IO75PDB1V4
C26	VCCIB1
C27	IO64PPB1V2
C28	VCC
C29	GBA1/IO81PPB1V4
C30	GND
D1	IO303PPB7V3
D2	VCC
D3	IO305NPB7V3
D4	GND
D5	GAA1/IO00PPB0V0
D6	GAC1/IO02PDB0V0
D7	IO06NPB0V0
D8	GAB0/IO01NDB0V0
D9	IO05NDB0V0
D10	IO11NDB0V1
D11	IO11PDB0V1
D12	IO23NDB0V2
D13	IO23PDB0V2
D14	IO27PDB0V3
D15	IO40PDB0V4
D16	IO47NDB1V0
D17	IO47PDB1V0
D18	IO55NPB1V1
D19	IO65NDB1V3
D20	IO65PDB1V3
D21	IO71NDB1V3
D22	IO71PDB1V3
D23	IO73NDB1V4
D24	IO73PDB1V4
D25	IO74NDB1V4
D26	GBB0/IO80NPB1V4
D27	GND
D28	GBA0/IO81NPB1V4
D29	VCC
D30	GBA2/IO82PPB2V0
E1	GND
E2	IO303NPB7V3
E3	VCCIB7
E4	IO305PPB7V3
E5	VCC
E6	GAC0/IO02NDB0V0
E7	VCCIB0
E8	IO06PPB0V0
E9	IO24NDB0V2
E10	IO24PDB0V2
E11	IO13NDB0V1
E12	IO13PDB0V1
E13	IO34NDB0V4
E14	IO34PDB0V4
E15	IO40NDB0V4
E16	IO49NDB1V1

Revision	Changes	Page
Revision 10 (March 2012)	The "In-System Programming (ISP) and Security" section and "Security" section were revised to clarify that although no existing security measures can give an absolute guarantee, Microsemi FPGAs implement the best security available in the industry (SAR 34669).	I, 1-1
	The Y security option and Licensed DPA Logo were added to the "ProASIC3E Ordering Information" section. The trademarked Licensed DPA Logo identifies that a product is covered by a DPA counter-measures license from Cryptography Research (SAR 34727).	III
	The following sentence was removed from the "Advanced Architecture" section: "In addition, extensive on-chip programming circuitry allows for rapid, single-voltage (3.3 V) programming of IGLOOe devices via an IEEE 1532 JTAG interface" (SAR 34689).	1-3
	The "Specifying I/O States During Programming" section is new (SAR 34699).	1-6
	VCCPLL in Table 2-2 • Recommended Operating Conditions [1] was corrected from "1.4 to 1.6 V" to "1.425 to 1.575 V" (SAR 33851). The T_J symbol was added to the table and notes regarding T_A and T_J were removed. The second of two parameters in the VCCI and VMV row, called "3.3 V DC supply voltage," was corrected to "3.0 V DC supply voltage" (SAR 37227).	2-2
	The reference to guidelines for global spines and VersaTile rows, given in the "Global Clock Contribution—P_{CLOCK}" section, was corrected to the "Spine Architecture" section of the Global Resources chapter in the *ProASIC3E FPGA Fabric User's Guide* (SAR 34735).	2-9
	t_{DOUT} was corrected to t_{DIN} in Figure 2-3 • Input Buffer Timing Model and Delays (example) (SAR 37109).	2-13
	The typo related to the values for 3.3 V LVCMOS Wide Range in Table 2-17 • Summary of I/O Timing Characteristics—Software Default Settings was corrected (SAR 37227).	2-19
	The notes regarding drive strength in the "Summary of I/O Timing Characteristics – Default I/O Software Settings" section and "3.3 V LVCMOS Wide Range" section and tables were revised for clarification. They now state that the minimum drive strength for the default software configuration when run in wide range is ±100 µA. The drive strength displayed in software is supported in normal range only. For a detailed I/V curve, refer to the IBIS models (SAR 34763).	2-18, 2-27

Revision	Changes	Page
v2.0 (continued)	Table 3-6 • Temperature and Voltage Derating Factors for Timing Delays was updated.	3-5
	Table 3-5 • Package Thermal Resistivities was updated.	3-5
	Table 3-10 • Different Components Contributing to the Dynamic Power Consumption in ProASIC3E Devices was updated.	3-8
	t_{WRO} and t_{CCKH} were added to Table 3-94 • RAM4K9 and Table 3-95 • RAM512X18.	3-74 to 3-74
	The note in Table 3-24 • I/O Input Rise Time, Fall Time, and Related I/O Reliability was updated.	3-23
	Figure 3-43 • Write Access After Write onto Same Address, Figure 3-44 • Read Access After Write onto Same Address, and Figure 3-45 • Write Access After Read onto Same Address are new.	3-71 to 3-73
	Figure 3-53 • Timing Diagram was updated.	3-80
	Notes were added to the package diagrams identifying if they were top or bottom view.	N/A
	The A3PE1500 "208-Pin PQFP" table is new.	4-4
	The A3PE1500 "484-Pin FBGA" table is new.	4-18
	The A3PE1500 "A3PE1500 Function" table is new.	4-24
Advance v0.6 (January 2007)	In the "Packaging Tables" table, the number of I/Os for the A3PE1500 was changed for the FG484 and FG676 packages.	ii
Advance v0.5 (April 2006)	B-LVDS and M-LDVS are new I/O standards added to the datasheet.	N/A
	The term flow-through was changed to pass-through.	N/A
	Figure 2-8 • Very-Long-Line Resources was updated.	2-8
	The footnotes in Figure 2-27 • CCC/PLL Macro were updated.	2-28
	The Delay Increments in the Programmable Delay Blocks specification in Figure 2-24 • ProASIC3E CCC Options.	2-24
	The "SRAM and FIFO" section was updated.	2-21
	The "RESET" section was updated.	2-25
	The "WCLK and RCLK" section was updated.	2-25
	The "RESET" section was updated.	2-25
	The "RESET" section was updated.	2-27
	B-LVDS and M-LDVS are new I/O standards added to the datasheet.	N/A
	The term flow-through was changed to pass-through.	N/A
	Figure 2-8 • Very-Long-Line Resources was updated.	2-8
	The footnotes in Figure 2-27 • CCC/PLL Macro were updated.	2-28
	The Delay Increments in the Programmable Delay Blocks specification in Figure 2-24 • ProASIC3E CCC Options.	2-24
	The "SRAM and FIFO" section was updated.	2-21
	The "RESET" section was updated.	2-25
	The "WCLK and RCLK" section was updated.	2-25